

BIRLA INSTITUTE OF TECHNOLOGY, MESRA, RANCHI  
(END SEMESTER EXAMINATION)

CLASS: IMSc.  
BRANCH: CHEMISTRY

SEMESTER: VIII  
SESSION: SP/19

SUBJECT: SAC2011- ADVANCED INORGANIC CHEMISTRY

TIME: 3 Hours

FULL MARKS: 60

**INSTRUCTIONS:**

1. The question paper contains 7 questions each of 12 marks and total 84 marks.
  2. Candidates may attempt any 5 questions maximum of 60 marks.
  3. The missing data, if any, may be assumed suitably.
  4. Before attempting the question paper, be sure that you have got the correct question paper.
  5. Tables/Data hand book/Graph paper etc. to be supplied to the candidates in the examination hall.
- 

- Q.1(a) A 3d transition metal ion possesses the following value of spin-orbit coupling constant  $\zeta = 515 \text{ cm}^{-1}$  and  $\lambda$  for strong octahedral and tetrahedral field are  $-172 \text{ cm}^{-1}$  and  $-515 \text{ cm}^{-1}$ . Predict the transition metal ion. [2]
- Q.1(b) Explain why Sm(III) and Eu(III) have anomalous magnetic moment in comparison to the other lanthanide ions. [4]
- Q.1(c) Derive the expression of molar magnetic susceptibility for a multi electron system where multiplet width is greater than thermal energy. [6]
- Q.2(a) Ni(II) in both tetrahedral and octahedral environment have  $\mu_{\text{eff}} > \mu_{\text{so}}$  - Explain. [2]
- Q.2(b) Magnetic moment of  $[(\text{NH}_3)_5\text{CrO}(\text{NH}_3)_5]\text{Br}_4$  is less than  $[(\text{NH}_3)_5\text{CrOH}(\text{NH}_3)_5]\text{Br}_5$  - Explain. [4]
- Q.2(c) With example discuss Spin Admixture in magnetochemistry. [6]
- Q.3(a) What is secular equilibrium in radioactivity? [2]
- Q.3(b) Write short note on Fission. [4]
- Q.3(c) Derive the expression for the number of daughter nuclei for a radioactive decay equilibrium. [6]
- Q.4(a) What is grain boundary? [2]
- Q.4(b) Discuss volume defects in solid. [4]
- Q.4(c) Derive the expression for calculation of defect concentration at any given temperature when the energy required for their formation is known. [6]
- Q.5(a) What is Seebeck effect? [2]
- Q.5(b) Define extrinsic, intrinsic, n-type and p-type semiconductors. [4]
- Q.5(c) Draw the band bending diagram at metal-semiconductor (n-type) interface for the case of  $\phi_M > \phi_S$  and discuss the phenomena. [6]
- Q.6(a) Define enantiotrops and monotrops. [2]
- Q.6(b) Name the different polymorphs of  $\text{SiO}_2$  and draw the temperature Vs pressure diagram showing the polymorph [4]
- Q.6(c) What is order-disorder transformations? If the order parameter is J, derive the expression for internal energy U. [6]
- Q.7(a) What do you mean by single crystal? [2]
- Q.7(b) Explain vacuum evaporation technique. [4]
- Q.7(c) Discuss Bridgman and Stockbarger methods with temperature profile. [6]

:::::29/04/2019 M:::::